

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

GT25G102(SM)

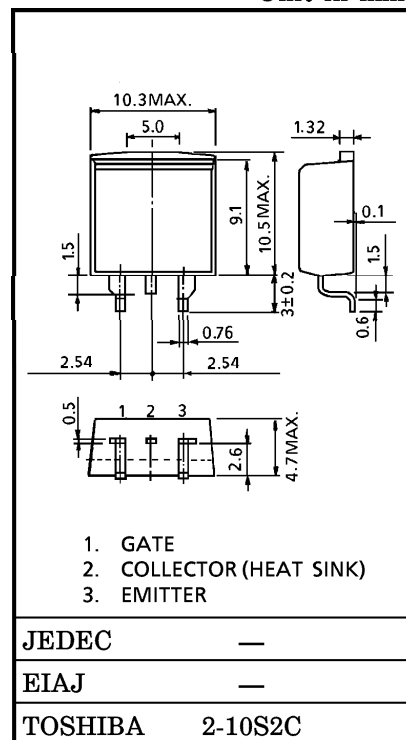
STROBE FLASH APPLICATIONS

Unit in mm

- High Input Impedance
- Low Saturation Voltage : $V_{CE(sat)} = 8V$ (Max.) ($I_C = 150A$)
- Enhancement-Mode
- 12V Gate Drive

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	400	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	DC	I_C	25	A
	1ms	I_{CP}	150	
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	1.3	A
	$T_c = 25^\circ C$	P_C	75	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$



Weight : 1.4g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 100	nA
Collector Cut-off Current		I_{CES}	$V_{CE} = 400V, V_{GE} = 0$	—	—	10	μA
Gate-Emitter Cut-off Voltage		$V_{CE(OFF)}$	$I_C = 1mA, V_{CE} = 5V$	2	—	5	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 150A, V_{GE} = 12V$ (Pulsed)	—	4	8	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	2600	—	pF
Switching Time	Rise Time	t_r	<p>$V_{IN} : t_r \leq 100ns$ $t_f \leq 100ns$ Duty cycle $\leq 1\%$</p>	—	0.1	0.5	μs
	Turn-on Time	t_{on}		—	0.15	0.5	
	Fall Time	t_f		—	4.0	6.0	
	Turn-off Time	t_{off}		—	4.5	7.0	
Thermal Resistance		$R_{th(j-c)}$	—	—	—	1.66	$^\circ C/W$

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